

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE3011E uses advanced trench technology to provide excellent R_{DS(ON)}, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications. It is ESD protested.

General Features

V_{DS} = 30V,I_D =11A

 $R_{DS(ON)}$ < 10m Ω @ V_{GS} =10V

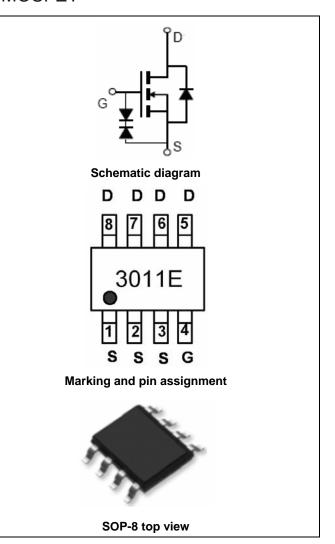
 $R_{DS(ON)}$ < 14m Ω @ V_{GS} =4.5V

ESD Rating: 2000V HBM

- High power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- ●PWM application
- ●Load switch



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3011E	NCE3011E	SOP-8	Ø330mm	12mm	2500 units

Absolute Maximum Ratings (T_A=25 ℃ unless otherwise noted)

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Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _G s	±10	V
Drain Current-Continuous	I _D	11	Α
Drain Current-Pulsed (Note 1)	I _{DM}	50	Α
Maximum Power Dissipation	P _D	2.5	W
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}$ C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	50	°C/W	
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Electrical Characteristics (T_A=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics			•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V,V _{GS} =0V	-	-	1	μΑ
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±10V,V _{DS} =0V	-	-	±10	μΑ
On Characteristics (Note 3)			•			
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.0	1.5	2.0	V
Drain Course On State Registeres	В	V _{GS} =10V, I _D =8A	-	7	10	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =6A	-	10	14	mΩ
Forward Transconductance	g fs	V _{DS} =10V,I _D =11A	25	-	-	S
Dynamic Characteristics (Note4)			•			
Input Capacitance	C _{lss}	\/ -45\/\/ -0\/	-	1155	-	PF
Output Capacitance	Coss	V_{DS} =15V, V_{GS} =0V, F=1.0MHz	-	260	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.UIVIHZ	-	95	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	10		nS
Turn-on Rise Time	t _r	V_{DD} =15 V , R_L =2.2 Ω	-	16		nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =5 V , R_{GEN} =3 Ω	-	40		nS
Turn-Off Fall Time	t _f		-	10.8		nS
Total Gate Charge	Qg	\/ 45\/1 04	-	17.5		nC
Gate-Source Charge	Q _{gs}	V _{DS} =15V,I _D =8A,	-	4.5	-	nC
Gate-Drain Charge	Q_{gd}	V _{GS} =4.5V	-	2.5	-	nC
Drain-Source Diode Characteristics			•			•
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =1A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	11	Α

Notes:

- $\textbf{1.} \ \textbf{Repetitive Rating: Pulse width limited by maximum junction temperature.}$
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

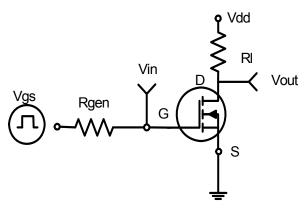


Figure 1:Switching Test Circuit

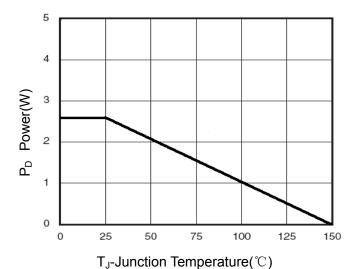


Figure 3 Power Dissipation

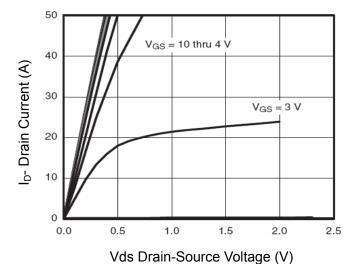


Figure 5 Output Characteristics

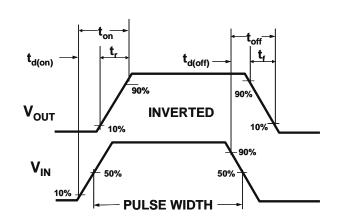


Figure 2:Switching Waveforms

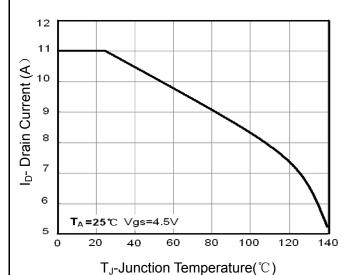


Figure 4 Drain Current

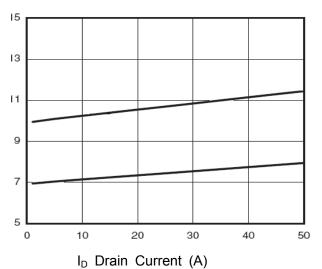
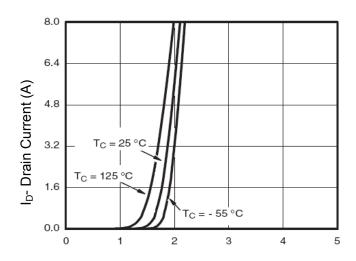
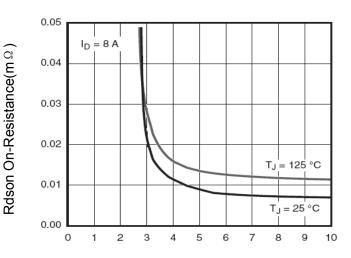


Figure 6 Drain-Source On-Resistance





Vgs Gate-Source Voltage (V)
Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs

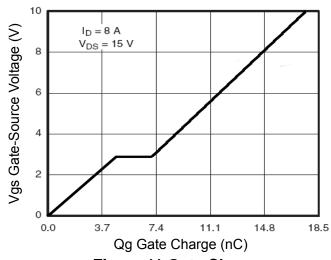


Figure 11 Gate Charge

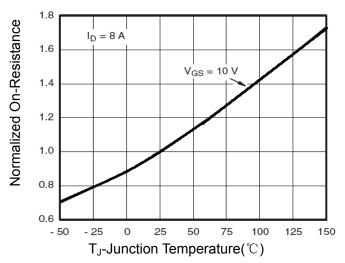


Figure 8 Drain-Source On-Resistance

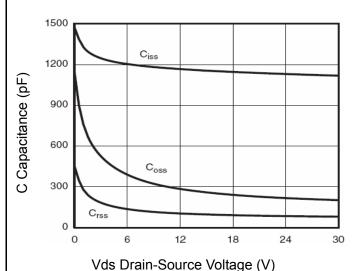


Figure 10 Capacitance vs Vds

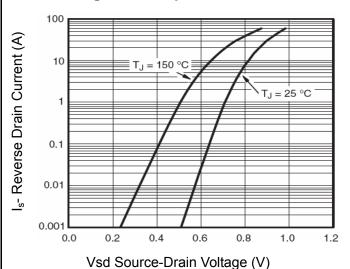


Figure 12 Source- Drain Diode Forward

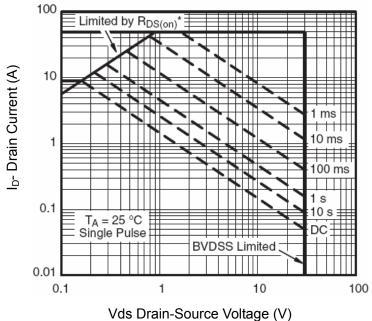


Figure 13 Safe Operation Area

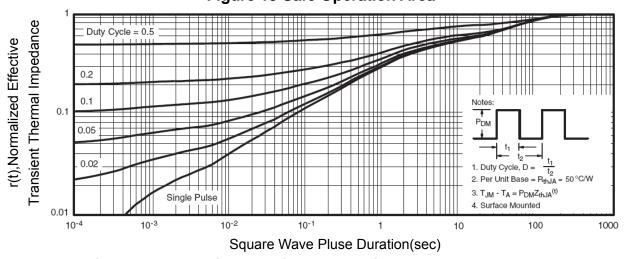
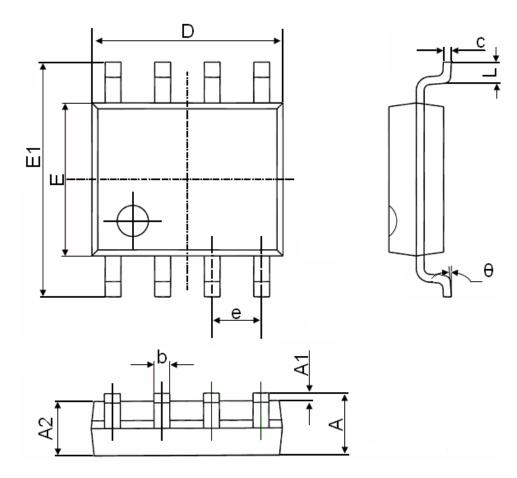


Figure 14 Normalized Maximum Transient Thermal Impedance

Pb Free Product

SOP-8 Package Information



Comple of	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
С	0.170	0.250	0.006	0.010	
D	4.700	5.100	0.185	0.200	
E	3.800	4.000	0.150	0.157	
E1	5.800	6.200	0.228	0.244	
е	1.270	(BSC)	0.050	(BSC)	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	

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